

Specifications HA-2420/883

Absolute Maximum Ratings

Voltage Between V+ and V- Terminals	40V
Differential Input Voltage	±24V
Digital Input Voltage (S/H Pin)	+8V, -15V
Output Current	Short Circuit Protected
Storage Temperature Range	-65°C < T _A < +150°C
Lead Temperature (Soldering 10 Seconds)	275°C
Junction Temperature	+175°C
Thermal Resistance, Junction-to-Case (θ _{JC})	
Ceramic DIP Package	24°C/W
Ceramic LCC Package	20°C/W

Thermal Resistance, Junction-to-Ambient (θ _{JA})	
Ceramic DIP Package	96°C/W
Ceramic LCC Package	88°C/W
Power Dissipation	
Ceramic DIP Package	1.03W @ +75°C
Ceramic LCC Package	1.14W @ +75°C
Power Dissipation Derating Factor (Above +75°C)	
Ceramic DIP Package	10mW/°C
Ceramic LCC Package	11.4mW/°C
ESD Classification	≤ 2000V

Recommended Operating Conditions

Operating Temperature Range	-55°C < T _A < +125°C
Operating Supply Voltage (±V _{SUPPLY})	±15V
Analog Input Voltage (V _S)	±10V

Logic Level Low (V _{IL})	0V to 0.8V
Logic Level High (V _{IH})	2.0V to 5.0V

TABLE 1. D.C. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at V+ = +15V; V- = -15V; V_{IL} = 0.8V (Sample); V_{IH} = 2.0V (Hold); C_H = 1000pF, -Input Tied to Output, Unless Otherwise Specified

D.C. PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Input Offset Voltage	V _{IO}		1	+25°C	-4	4	mV
			2, 3	-55°C, +125°C	-6	6	mV
Input Bias Current	I _{B+}		1	+25°C	-200	200	nA
			2, 3	-55°C, +125°C	-400	400	nA
	I _{B-}		1	+25°C	-200	200	nA
			2, 3	-55°C, +125°C	-400	400	nA
Input Offset Current	I _{IO}		1	+25°C	-50	50	nA
			2, 3	-55°C, +125°C	-100	100	nA
Open Loop Voltage Gain	+A _{VS}	R _L = 2kΩ, C _L = 50pF, V _{OUT} = +10V	1	+25°C	25k	—	V/V
			2, 3	-55°C, +125°C	25k	—	V/V
	-A _{VS}		1	+25°C	25k	—	V/V
			2, 3	-55°C, +125°C	25k	—	V/V
Common Mode Rejection Ratio	-CMRR	V+ = 25V, V- = -5V, V _{OUT} = +10V, V _{S/H} = 10.8V	1	+25°C	80	—	dB
			2, 3	-55°C, +125°C	80	—	dB
	+CMRR		1	+25°C	80	—	dB
			2, 3	-55°C, +125°C	80	—	dB
Output Current	+I _O -I _O	V _{OUT} = +10V V _{OUT} = -10V	1	+25°C	+15.0	—	mA
			1	+25°C	-15.0	—	mA
Output Voltage Swing	+V _{OP}	R _L = 2kΩ, C _L = 50pF	1	+25°C	+10.0	—	V
			2, 3	-55°C, +125°C	+10.0	—	V
	-V _{OP}		1	+25°C	—	-10.0	V
			2, 3	-55°C, +125°C	—	-10.0	V
Power Supply Current	+I _{CC} -I _{CC}		1	+25°C	—	5.5	mA
			1	+25°C	-3.5	—	mA
Power Supply Rejection Ratio	+PSRR	V+ = 10V, 20V V- = -15V, -15V	1	+25°C	80	—	dB
			2, 3	-55°C, +125°C	80	—	dB
	-PSRR		1	+25°C	80	—	dB
			2, 3	-55°C, +125°C	80	—	dB
Digital Input Current	I _{IN1}	V _{IN1} = 0V V _{IN2} = 5.0V	1	+25°C	—	800	μA
			2, 3	-55°C, +125°C	—	800	μA
	I _{IN2}		1	+25°C	—	20	μA
			2, 3	-55°C, +125°C	—	20	μA
Digital Input Voltage	V _{IL}		1	+25°C	—	0.8	V
			2, 3	-55°C, +125°C	—	0.8	V
	V _{IH}		1	+25°C	2.0	—	V
			2, 3	-55°C, +125°C	2.0	—	V
Drift Current	I _D	V _{IN} = 0V, R _L = 2kΩ, C _L = 50pF, S/H = 4.0V	2	+125°C	-10	10	nA

CAUTION: These devices are sensitive to electrostatic discharge. Proper IC handling procedures should be followed.

TABLE 2. A.C. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at $V^+ = +15V$, $V^- = -15V$, $V_{IL} = 0.8V$ (Sample), $V_{IH} = 2.0V$ (Hold), $C_H = 1000pF$, -Input Tied to Output, Unless Otherwise Specified

A.C. PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUP	TEMP	LIMITS		UNITS
					MIN	MAX	
Hold Step Error	VE _{RROR}	$V_{IN} = 0V, 4V, t_{rise}(V_{S/H}) = 30ns$	4	+25°C	-20	20	mV
Transient Response Rise Time & Fall Time	TR _(tr)	$C_L = 50pF, R_L = 2k\Omega, A_V = +1,$ $V_{OUT} = 200mV$ peak-to-peak	4	+25°C	—	100	ns
	TR _(tf)	$C_L = 50pF, R_L = 2k\Omega, A_V = +1,$ $V_{OUT} = 200mV$ peak-to-peak	4	+25°C	—	100	ns
Transient Response Overshoot	TR _(+OS)	$C_L = 50pF, R_L = 2k\Omega, A_V = +1,$ $V_{OUT} = 200mV$ peak-to-peak	4	+25°C	—	40	%
	TR _(-OS)	$C_L = 50pF, R_L = 2k\Omega, A_V = +1,$ $V_{OUT} = 200mV$ peak-to-peak	4	+25°C	—	40	%
Transient Response Slew Rate	TR _(+SR)	$C_L = 50pF, R_L = 2k\Omega, A_V = +1,$ $V_{OUT} = 10V$ peak-to-peak	4	+25°C	3.5	—	V/ μ s
	TR _(-SR)	$C_L = 50pF, R_L = 2k\Omega, A_V = +1,$ $V_{OUT} = 10V$ peak-to-peak	4	+25°C	3.5	—	V/ μ s

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Characterized at $V^+ = +15V$, $V^- = -15V$, $V_{IL} = 0.8V$ (Sample), $V_{IH} = 2.0V$ (Hold), $C_H = 1000pF$, -Input Tied to Output, Unless Otherwise Specified

PARAMETER	SYMBOL	CONDITIONS	NOTE	TEMP	LIMITS		UNITS
					MIN	MAX	
Hold Mode Feedthru Attenuation	V _{atten}	$R_L = 2k\Omega, C_L = 50pF, A_V = +1,$ $V_{IN} = 20V_{p-p}, f_{IN} = 50kHz$	1	+25°C, -55°C, +125°C	70	—	dB
Gain Bandwidth Product	GBWP	$R_L = 2k\Omega, C_L = 50pF, A_V = +1,$ $V_{IN} = 100mV_{p-p}$	1	+25°C,	2.5	—	MHz
Acquisition Time (0.1%)	+ _t acq (0.1%)	$R_L = 2k\Omega, C_L = 50pF, A_V = +1,$ $V_{OUT} = 0V, +10V$	1	+25°C,	—	4	μ s
	- _t acq (0.1%)	$R_L = 2k\Omega, C_L = 50pF, A_V = +1,$ $V_{OUT} = 0V, -10V$	1	+25°C,	—	4	μ s
Acquisition Time (0.01%)	+ _t acq (0.01%)	$R_L = 2k\Omega, C_L = 50pF, A_V = +1,$ $V_{OUT} = 0V, +10V$	1	+25°C,	—	6	μ s
	- _t acq (0.01%)	$R_L = 2k\Omega, C_L = 50pF, A_V = +1,$ $V_{OUT} = 0V, -10V$	1	+25°C,	—	6	μ s

NOTE: 1. The parameters listed in this table are controlled via design or process parameters and are not directly tested. These parameters are characterized upon initial design release and upon design changes which would affect these characteristics.

TABLE 4. ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUPS (SEE TABLES 1, 2 & 3)
Interim Electrical Parameters (Pre Burn-In)	1
Final Electrical Test Parameters	1*, 2, 3, 4
Group A Test Requirements	1, 2, 3, 4
Groups C & D Endpoints	1

* PDA applies to Subgroup 1 only. No other subgroups are included in PDA.

7
SAMPLE & HOLD
AMPLIFIERS

CAUTION: These devices are sensitive to electrostatic discharge. Proper IC handling procedures should be followed.

Test Circuits

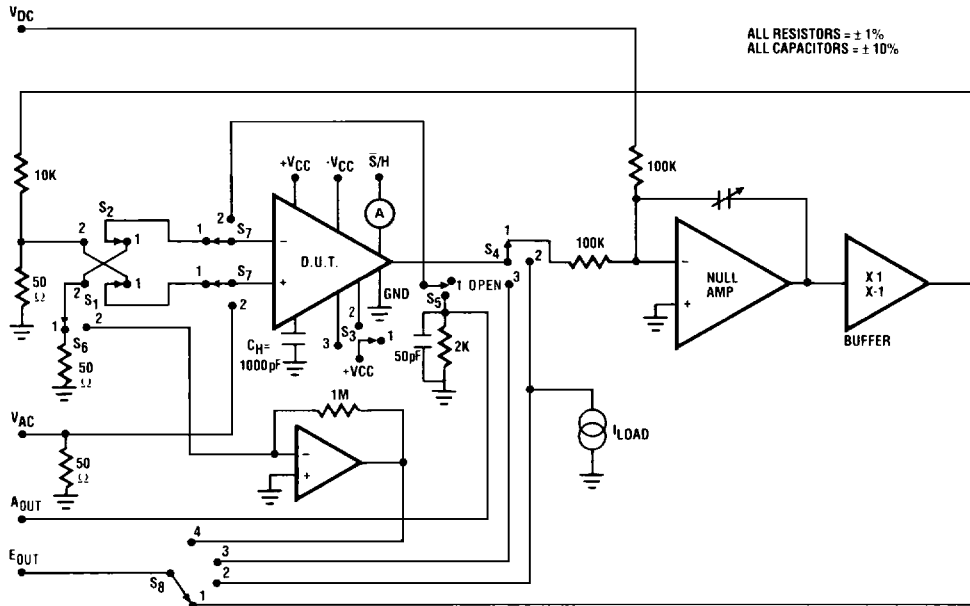
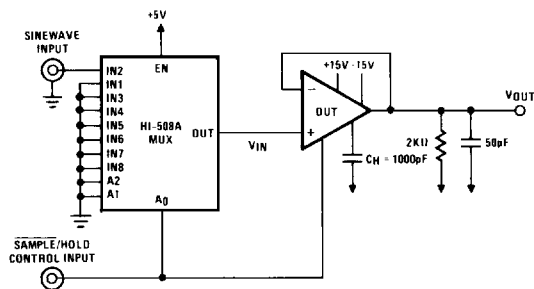


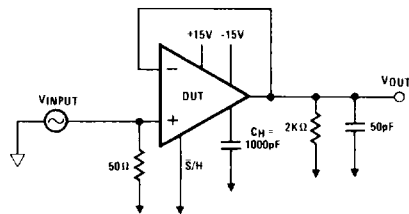
FIGURE 1.

Test Fixture Schematic (Switch Positions S₁ - S₈ Determine Configuration. See Chart A)

HOLD MODE FEEDTHROUGH ATTENUATION



GAIN BANDWIDTH PRODUCT



NOTE:

Compute Hold Mode Feedthrough Attenuation from the Formula:

$$\text{Feedthrough Attenuation} = 20 \log \left(\frac{V_{\text{OUT HOLD}}}{V_{\text{IN HOLD}}} \right)$$

Where V_{OUT HOLD} = Peak-Peak Value of Output Sinewave During the Hold Mode

GBWP is the Frequency of V_{INPUT} at which:

$$20 \log \left(\frac{V_{\text{OUT}}}{V_{\text{INPUT}}} \right) = -3\text{dB}$$

CHART A. TEST CIRCUIT CONDITIONS (SEE TEST CIRCUIT — FIGURE 1)

PARAMETER	NOTES	APPLY (IN VOLTS DC)				SWITCH POSITION								MEASURE		MEASURED PARAMETER EQUATION	UNITS	
		+V	-V	VDC	S/H	EQUOT	S1	S2	S3	S4	S5	S6	S7	S8	VALUE			UNITS
V _{IO}		15	-15	0	0.8	—	1	1	1	1	1	1	1	1	E1	V	$V_{IO} = E1/200$	mV
I _{IO}		15	-15	0	0.8	—	—	—	—	—	—	—	—	—		V	$I_{IO} = (E7-E10)/10^6$	nA
I _{B+}		15	-15	0	0.8	—	2	1	1	1	2	1	4	E7	V	$I_{B+} = E7/10^6$	nA	
I _{B-}		15	-15	0	0.8	—	1	1	1	1	2	1	4	E10	V	$I_{B-} = E10/10^6$	nA	
+A _{VS}	1	15	-15	0	0.8	—	1	1	1	2	1	1	1	E25	V	$+A_{VS} = 20\log_{10} [(E25-E26)/200]$	dB	
-A _{VS}	1	15	-15	-10	0.8	—	1	1	1	2	1	1	1	E26	V			
	1	15	-15	0	0.8	—	1	1	1	2	1	1	1	E27	V			
	1	15	-15	+10	0.8	—	1	1	1	2	1	1	1	E28	V	$-A_{VS} = 20\log_{10} [(E27-E28)/200]$	dB	
-CMRR	4	25	-5	-10	10.8	—	1	1	1	1	1	1	1	E17	V	$-CMRR = 20\log_{10} [10/((E1-E17)/200)]$	dB	
+CMRR	5	5	-25	+10	-9.2	—	1	1	1	1	1	1	1	E18	V	$+CMRR = 20\log_{10} [10/((E1-E18)/200)]$	dB	
+I _O		15	-15	-13	0.8	10	1	1	3	1	1	1	3	I21	mA	$+I_O = I21$	mA	
-I _O		15	-15	+13	0.8	-10	1	1	3	1	1	1	3	I22	mA	$-I_O = I22$	mA	
+V _{OP}	1	15	-15	-14	0.8	—	1	1	3	2	1	1	3	E23	V	$+V_{OP} = E23$	V	
-V _{OP}	1	15	-15	+14	0.8	—	1	1	3	2	1	1	3	E24	V	$-V_{OP} = E24$	V	
+I _{CC}		15	-15	0	0.8	—	1	1	1	1	1	1	1		mA		mA	
-I _{CC}		15	-15	0	0.8	—	1	1	1	1	1	1	1		mA		mA	
+PSRR	10	-15	0	0.8	—	—	1	1	1	1	1	1	1	E13	V	$+PSRR = 20\log_{10} [10/(E13-E14)]$	dB	
	20	-15	0	0.8	—	—	1	1	1	1	1	1	1	E14	V			
-PSRR	15	-10	0	0.8	—	—	1	1	1	1	1	1	1	E15	V	$-PSRR = 20\log_{10} [10/(E15-E16)]$	dB	
	15	-20	0	0.8	—	—	1	1	1	1	1	1	1	E16	V			
I _{IN1}		15	-15	0	0	—	1	1	1	1	1	1	1	I _{S/H}	μA		μA	
I _{IN2}		15	-15	0	5	—	1	1	1	1	1	1	1	I _{S/H}	μA		μA	
I _D	1,6	15	-15	0	4.0	—	1	1	3	2	1	2	1	A _{OUT}	mV	$I_D = C_H \times \Delta V / \Delta T$	nA	
Hold Step Error	1,6	15	-15	0	0	—	1	1	3	2	1	2	1	A _{OUT1}	mV	$Error = A_{OUT1} - A_{OUT2} $	mV	
		15	-15	0	4.0	—	1	1	3	2	1	2	1	A _{OUT2}	mV			
TR _(tr)	2	15	-15	—	0.8	—	1	1	3	2	1	2	1	A _{OUT}	See Notes	$TR_{(tr)} = 10\% \text{ to } 90\%$	ns	
TR _(ft)	2	15	-15	—	0.8	—	1	1	3	2	1	2	1	A _{OUT}	See Notes	$TR_{(ft)} = 90\% \text{ to } 10\%$	ns	
TR _(+OS)	2	15	-15	—	0.8	—	1	1	3	2	1	2	1	A _{OUT}	See Notes	$TR_{(+OS)} = (V_{peak} - V_{final}) / V_{final} \times 100$	%	
TR _(-OS)	2	15	-15	—	0.8	—	1	1	3	2	1	2	1	A _{OUT}	See Notes	$TR_{(-OS)} = (V_{peak} - V_{final}) / V_{final} \times 100$	%	
TR _(+SR)	3	15	-15	—	0.8	—	1	1	3	2	1	2	1	A _{OUT}	See Notes	$TR_{(+SR)} = \Delta V / \Delta T$	V/μs	
TR _(-SR)	3	15	-15	—	0.8	—	1	1	3	2	1	2	1	A _{OUT}	See Notes	$TR_{(-SR)} = \Delta V / \Delta T$	V/μs	

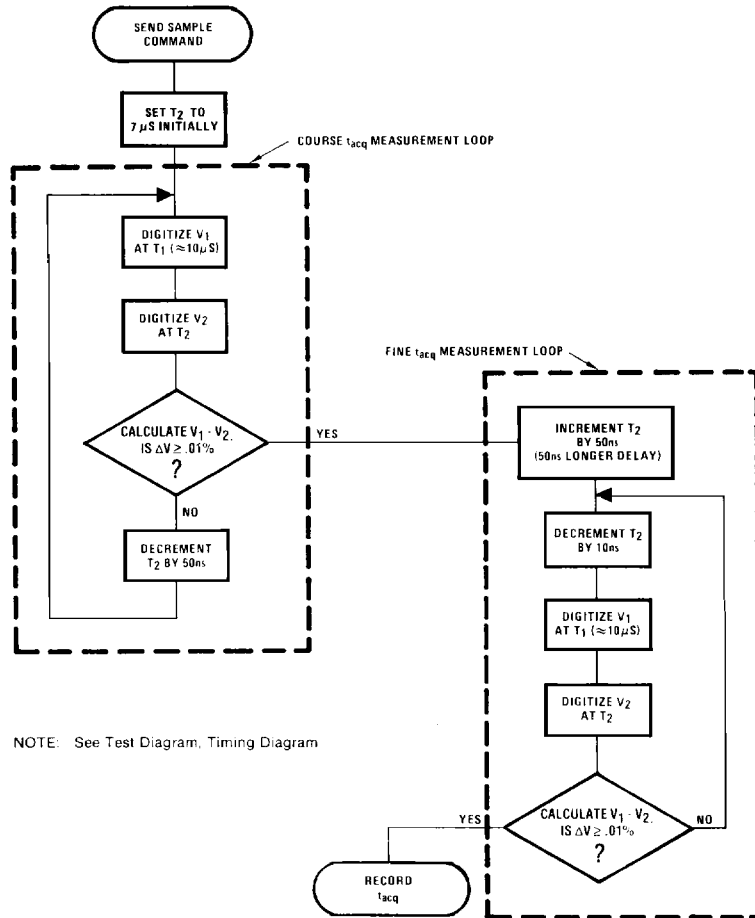
- NOTES: 1. R_{LDC} = 2kΩ
 2. V_{OUT} = 200mV_{p-p}, R_L = 2kΩ, C_L = 50pF
 3. V_{OUT} = 10V Step, R_L = 2kΩ, C_L = 50pF
 4. Package GND held at +10V for this test.
 5. Package GND held at -10V for this test.
 6. V_{AC} = 0V

7
 SAMPLE & HOLD
 AMPLIFIERS

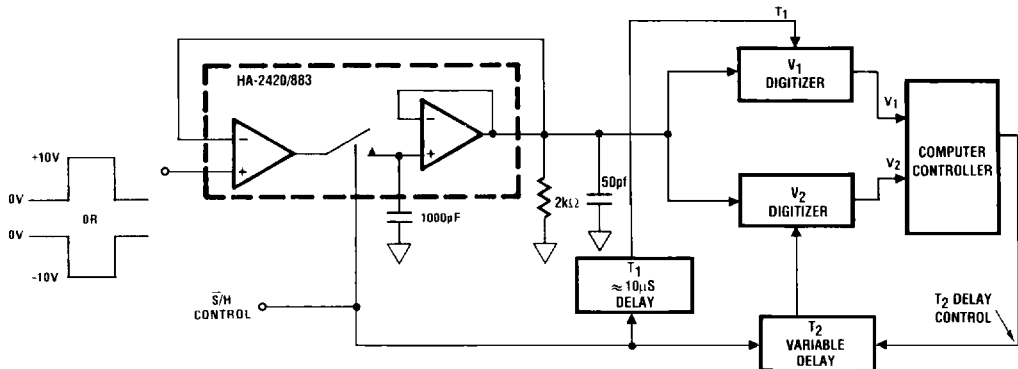
Test Circuits (Continued)

ACQUISITION TIME

(t_{acq} to 0.01% is shown, t_{acq} to 0.1% is done in the same manner)

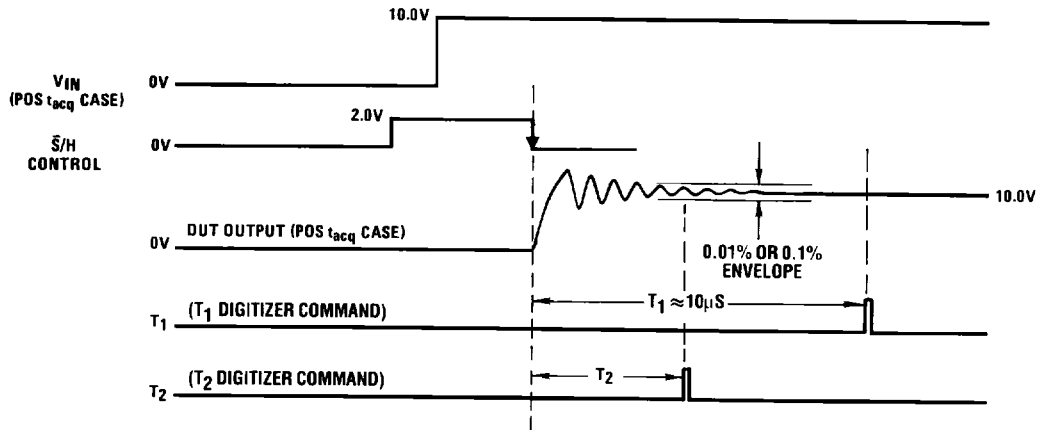


NOTE: See Test Diagram, Timing Diagram

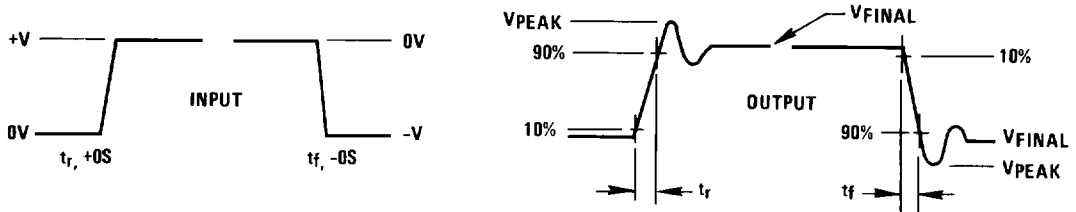


Timing Waveforms

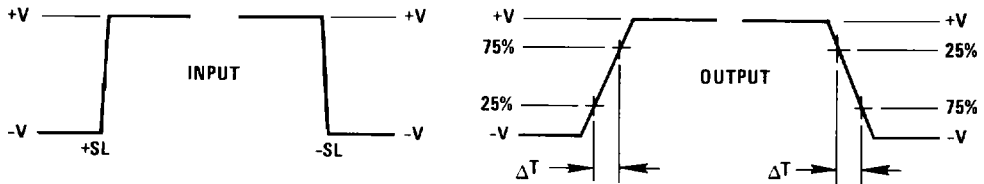
TIMING DIAGRAM FOR ACQUISITION TIME, (POSITIVE t_{acq} CASE)



OVERSHOOT, RISE & FALL TIME WAVEFORMS



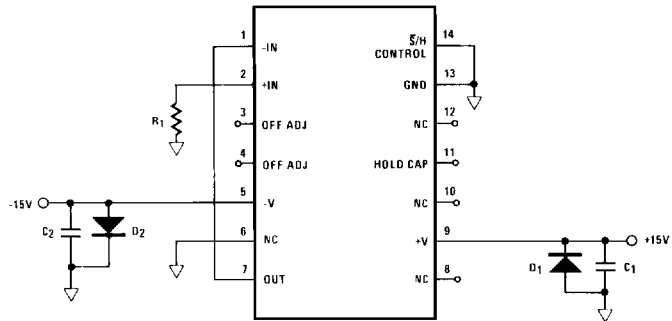
SLEW RATE WAVEFORMS



HA-2420/883

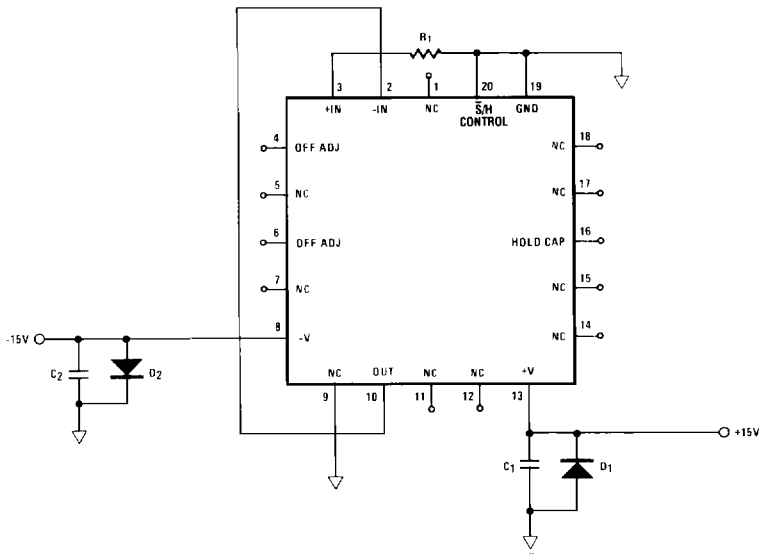
Burn-In Circuits

HA-2420/883 (CERAMIC DIP)



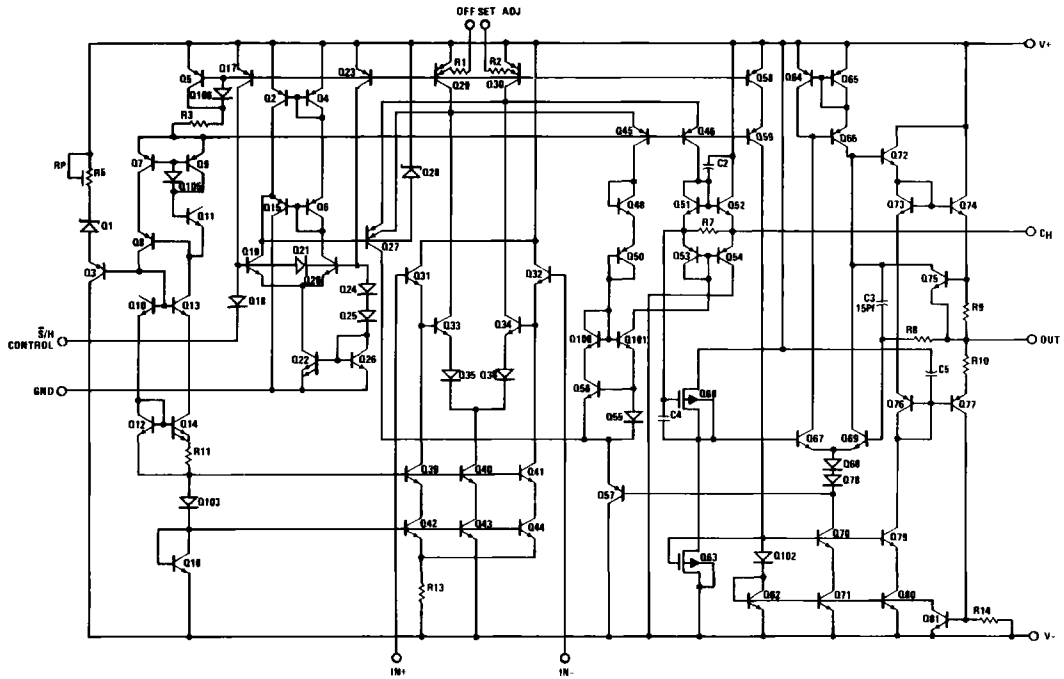
- R₁ = 100k Ω , $\pm 5\%$ (per socket)
- C₁ = C₂ = 0.1 μ F (one per row) or
0.01 μ F (one per socket)
- D₁ = D₂ = 1N4002 or equivalent (per board)

HA-2420/883 (CERAMIC LCC)



- R₁ = 100k Ω , $\pm 5\%$ (per socket)
- C₁ = C₂ = 0.1 μ F (one per row) or
0.01 μ F (one per socket)
- D₁ = D₂ = 1N4002 or equivalent (per board)

Schematic Diagram



HA-2420/883

Die Characteristics

DIE DIMENSIONS: 97 x 61 x 19 mils

METALLIZATION

Type: Al

Thickness: $16\text{k}\text{\AA} \pm 2\text{k}\text{\AA}$

GLASSIVATION

Type: SiOx

Thickness: $14\text{k}\text{\AA} \pm 2\text{k}\text{\AA}$

WORST CASE CURRENT DENSITY: $1.7 \times 10^5 \text{ A/cm}^2$

TRANSISTOR COUNT:

HA-2420/883 78

PROCESS: Bipolar-DI

DIE ATTACH

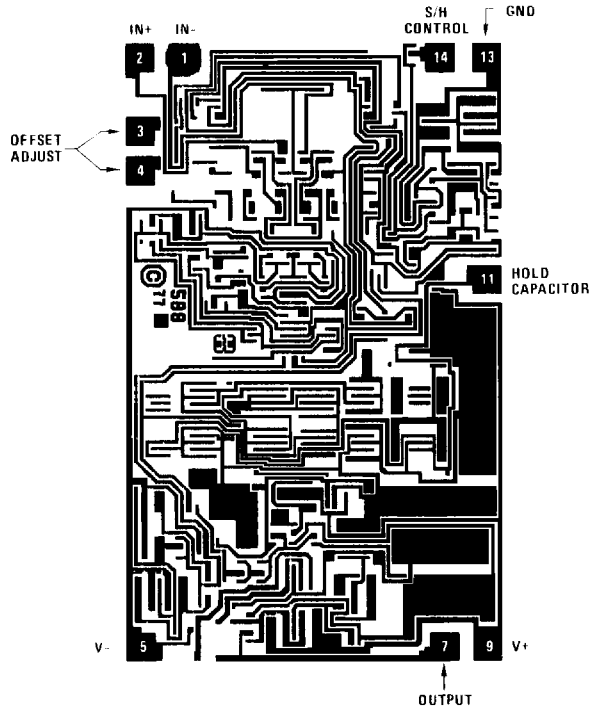
Material: Gold/Silicon Eutectic Alloy

Temperature: Ceramic DIP — 460°C (Max)

Ceramic LCC — 420°C (Max)

Metallization Mask Layout

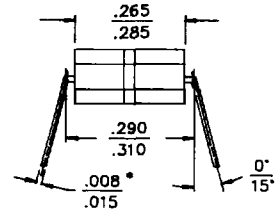
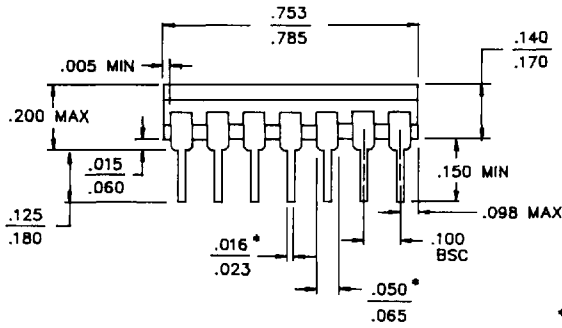
HA-2420/883



NOTE: Pad Numbers Correspond to DIP Package Only.

Packaging†

14 PIN CERAMIC DIP

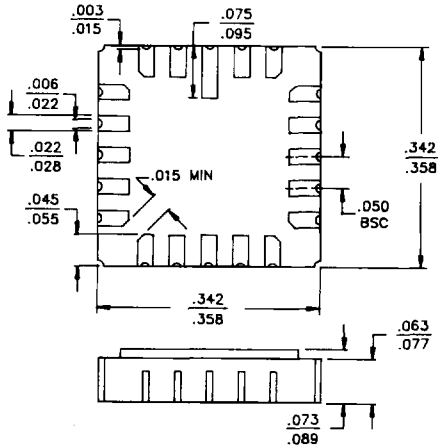


• INCREASE MAX LIMIT BY .003 INCHES MEASURED AT CENTER OF FLAT FOR SOLDER FINISH

LEAD MATERIAL: Type B
LEAD FINISH: Type A
PACKAGE MATERIAL: Ceramic, 90% Alumina
PACKAGE SEAL:
 Material: Glass Frit
 Temperature: 450°C ± 10°C
 Method: Furnace Seal

INTERNAL LEAD WIRE:
 Material: Aluminum
 Diameter: 1.25 Mil
 Bonding Method: Ultrasonic
COMPLIANT OUTLINE: 38510 D-1

20 PAD CERAMIC LCC



PAD MATERIAL: Type C
PAD FINISH: Type A
FINISH DIMENSION: Type A
PACKAGE MATERIAL: Multilayer Ceramic, 90% Alumina
PACKAGE SEAL:
 Material: Gold/Tin (80/20)
 Temperature: 320°C ± 10°C
 Method: Furnace Braze

INTERNAL LEAD WIRE:
 Material: Aluminum
 Diameter: 1.25 Mil
 Bonding Method: Ultrasonic
COMPLIANT OUTLINE: 38510 C-2

NOTE: All Dimensions are $\frac{\text{Min}}{\text{Max}}$. Dimensions are in inches.

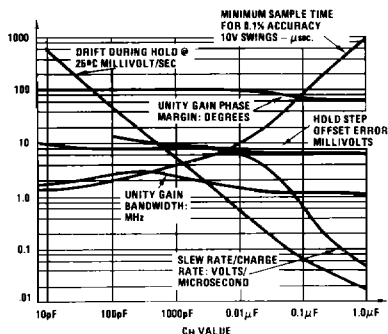
DESIGN INFORMATION

Fast Sample and Hold

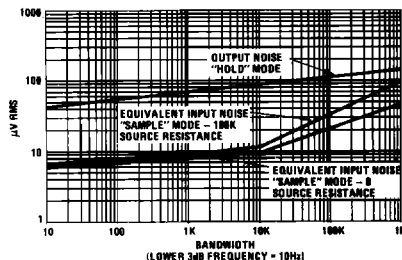
The information contained in this section has been developed through characterization by Harris Semiconductor and is for use as application and design data only. No guarantee is implied.

Typical Performance Curves Unless Otherwise Specified: $V_{SUPPLY} = \pm 15VDC$, $T_A = +25^\circ C$, $C_H = 1000pF$

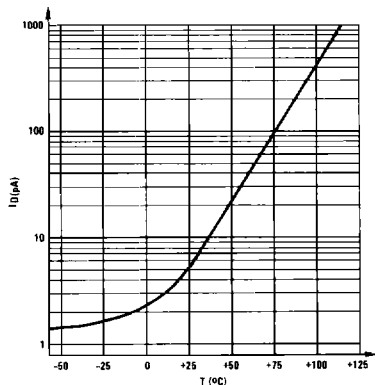
TYPICAL SAMPLE AND HOLD PERFORMANCE AS A FUNCTION OF HOLDING CAPACITOR



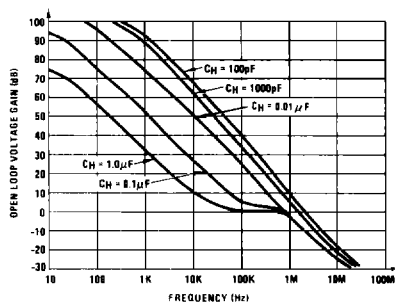
BROADBAND NOISE CHARACTERISTICS



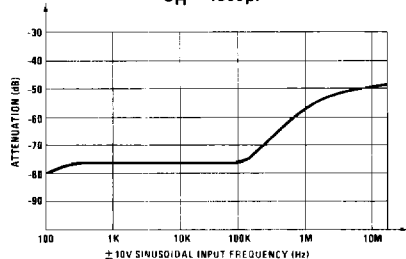
DRIFT CURRENT vs. TEMPERATURE



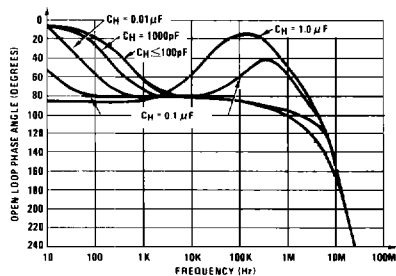
OPEN LOOP FREQUENCY RESPONSE



HOLD MODE FEEDTHROUGH ATTENUATION $C_H = 1000pF$



OPEN LOOP PHASE RESPONSE



DESIGN INFORMATION (Continued)

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Offset and Gain Adjustment

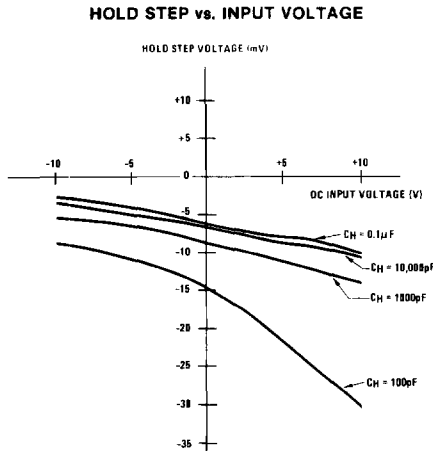


FIGURE 1.

BASIC SAMPLE-AND-HOLD (TOP VIEW)

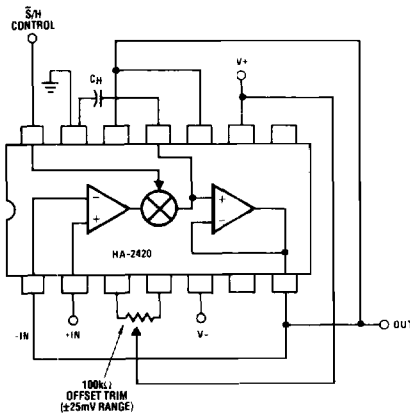


FIGURE 2.

OFFSET ADJUSTMENT

The offset voltage of the HA-2420 may be adjusted using a 100kΩ trim pot, as shown in Figure 2. The recommended adjustment procedure is:

1. Apply zero volts to the sample-and-hold input, and a square wave to the $\overline{S/H}$ control.
2. Adjust the trim pot for zero volts output in the hold mode.

GAIN ADJUSTMENT

The linear variation in pedestal voltage with sample-and-hold input voltage causes a -0.06% gain error ($C_H = 1000pF$). In some applications (D/A deglitcher, A/D converter) the gain error can be adjusted elsewhere in the system, while in other applications it must be adjusted at the sample-and-hold. The two circuits shown below demonstrate how to adjust gain error at the sample-and-hold.

The recommended procedure for adjusting gain error is:

1. Perform offset adjustment.
2. Apply the nominal input voltage that should produce a +10V output.
3. Adjust the trim pot for +10V output in the hold mode.
4. Apply the nominal input voltage that should produce a -10V output.
5. Measure the output hold voltage (V_{-10} NOMINAL). Adjust the trim pot for an output hold voltage of

$$\frac{(V_{-10} \text{ NOMINAL}) + (-10V)}{2}$$

INVERTING CONFIGURATION

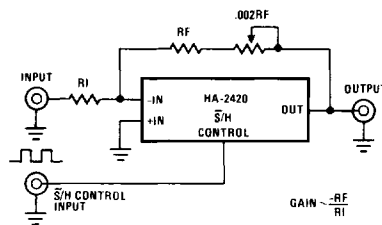


FIGURE 3.

NONINVERTING CONFIGURATION

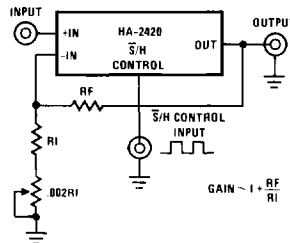


FIGURE 4.